



# STL6NM60N

N-channel 600 V - 0.85  $\Omega$  - 5.75 A - PowerFLAT™ (5x5)  
ultra low gate charge MDmesh™ II Power MOSFET

## Features

Type	V <sub>DSS</sub> @ T <sub>JMAX</sub>	R <sub>DS(on)</sub> Max	I <sub>D</sub>
STL6NM60N	650 V	< 0.92 $\Omega$	5.75 A <sup>(1)</sup>

1. The value is rated according Rthj-case

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

## Application

- Switching applications

## Description

This series of devices implements the second generation of MDmesh™ Technology. This revolutionary Power MOSFET associates a new vertical structure to the Company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

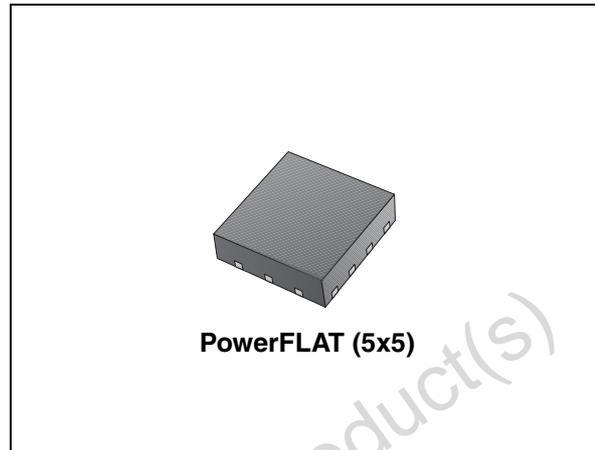


Figure 1. Internal schematic diagram

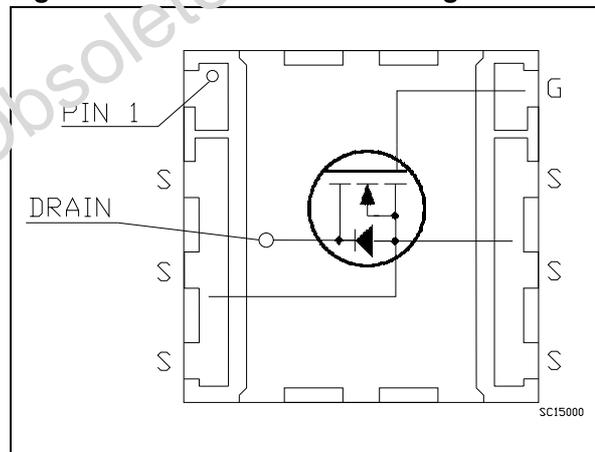


Table 1. Device summary

Order code	Marking	Package	Packaging
STL6NM60N	L6NM60N	PowerFLAT™ (5x5)	Tape & reel

# Contents

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Obsolete Product(s) - Obsolete Product(s)

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	600	V
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$ (steady state)	5.75	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	3.62	A
$I_{DM}^{(1),(2)}$	Drain current (pulsed)	23	A
$I_D^{(3)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	1	A
$I_D^{(3)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	0.65	A
$I_{DM}^{(2),(3)}$	Drain current (pulsed)	4	A
$P_{TOT}^{(3)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ (steady state)	2.1	W
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ (steady state)	70	W
	Derating factor <sup>(3)</sup>	0.02	W/°C
$dv/dt^{(4)}$	Peak diode recovery voltage slope	5	V/ns
$T_J$	Operating junction temperature	-55 to 150	°C
$T_{stg}$	storage temperature		

1. The value is rated according Rthj-case
2. Pulse width limited by safe operating area.
3. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu
4.  $I_{SD} \leq 4.6\text{A}$ ,  $dv/dt \leq 400\text{A}/\mu\text{s}$ ,  $V_{DD} = 80\%V_{(BR)DSS}$

**Table 3. Thermal resistance**

Symbol	Parameter	Typ	Max	Unit
$R_{thj-case}$	Thermal resistance junction-case	--	1.8	°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.2	58.5	°C/W

1. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu,  $t < 10\text{ sec}$

**Table 4. Avalanche characteristics**

Symbol	Parameter	Typ	Unit
$I_{AS}$	Avalanche current, repetitive or not-repetitive <sup>(1)</sup>	2	A
$E_{AS}$	Single pulse avalanche energy <sup>(2)</sup>	65	mJ

1. Pulse width limited by  $T_{jmax}$
2. Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = I_{AS}$ ,  $V_{DD} = 50\text{ V}$

## 2 Electrical characteristics

(T<sub>CASE</sub>=25°C unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0	600			V
dv/dt <sup>(1)</sup>	Drain-source voltage slope	V <sub>DD</sub> = 480 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.6 A	40			V/ns
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max rating, V <sub>DS</sub> = Max rating @ 125 °C			1 100	μA μA
I <sub>GSS</sub>	Gate body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±20 V			±100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.3 A		0.85	0.92	Ω

1. Characteristics value at turn off on inductive load

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 2.3 A		4		S
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> = 50V, f = 1 MHz, V <sub>GS</sub> = 0		420		pF
C <sub>oss</sub>	Output capacitance			30		pF
C <sub>rss</sub>	Reverse transfer capacitance			4		pF
C <sub>oss eq.</sub> <sup>(2)</sup>	Output equivalent capacitance	V <sub>GS</sub> = 0, V <sub>DS</sub> = 0 to 480 V		70		pF
R <sub>g</sub>	Gate input resistance	f = 1 MHz Gate DC Bias = 0 test signal level = 20 mV open drain		6		Ω
Q <sub>g</sub>	Total gate charge	V <sub>DD</sub> = 480 V, I <sub>D</sub> = 4.6 A		13		nC
Q <sub>gs</sub>	Gate-source charge	V <sub>GS</sub> = 10 V		2		nC
Q <sub>gd</sub>	Gate-drain charge	(see Figure 15)		7		nC

1. Pulsed: pulse duration = 300 μs, duty cycle 1.5%

2. C<sub>oss eq.</sub> is defined as a constant equivalent capacitance giving the same charging time as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}= 300\text{ V}$ , $I_D = 2.3\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ <i>(see Figure 14)</i>		10		ns
$t_r$	Rise time			8		ns
$t_{d(off)}$	Turn-off delay time			40		ns
$t_f$	Fall time			9		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$I_{SD}$	Source-drain current				1	A
$I_{SDM}^{(1)(2)}$	Source-drain current (pulsed)				4	A
$V_{SD}^{(3)}$	Forward on voltage	$I_{SD}= 4.6\text{ A}$ , $V_{GS}=0$			1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD}= 4.6\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=20\text{ V}$ <i>(see Figure 16)</i>		300		ns
$Q_{rr}$	Reverse recovery charge			2		nC
$I_{RRM}$	Reverse recovery current			12		A
$t_{rr}$	Reverse recovery time	$I_{SD}= 4.6\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=20\text{ V}$ , $T_j= 150\text{ }^\circ\text{C}$ <i>(see Figure 16)</i>		470		ns
$Q_{rr}$	Reverse recovery charge			3		nC
$I_{RRM}$	Reverse recovery current			12		A

1. Pulse width limited by safe operating area
2. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu
3. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

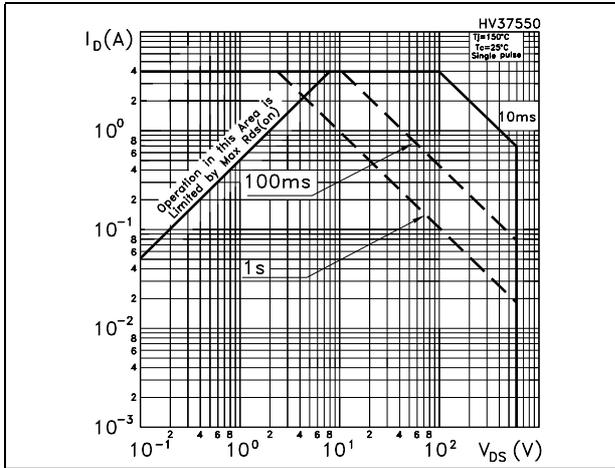


Figure 3. Thermal impedance

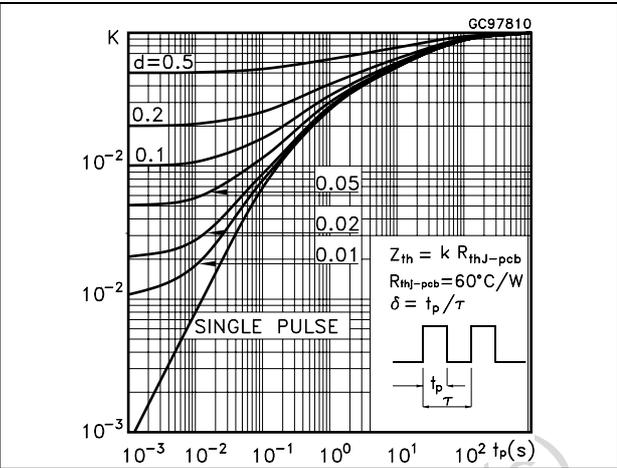


Figure 4. Output characteristics

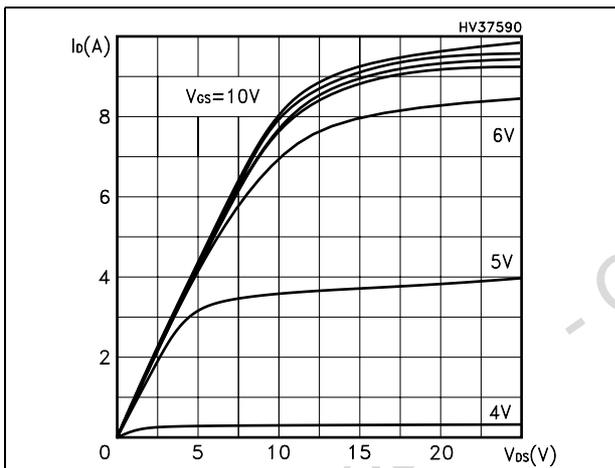


Figure 5. Transfer characteristics

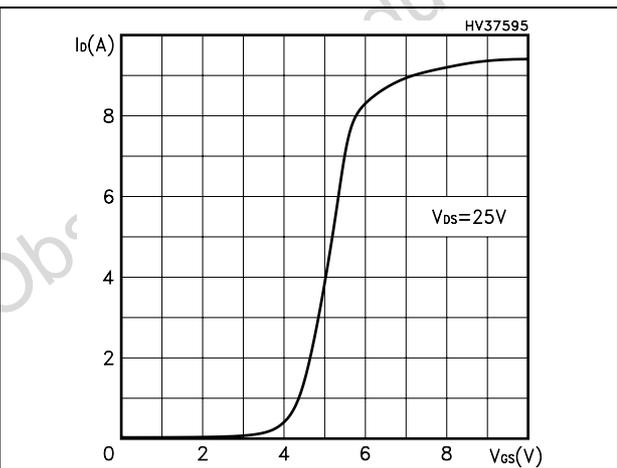


Figure 6. Transconductance

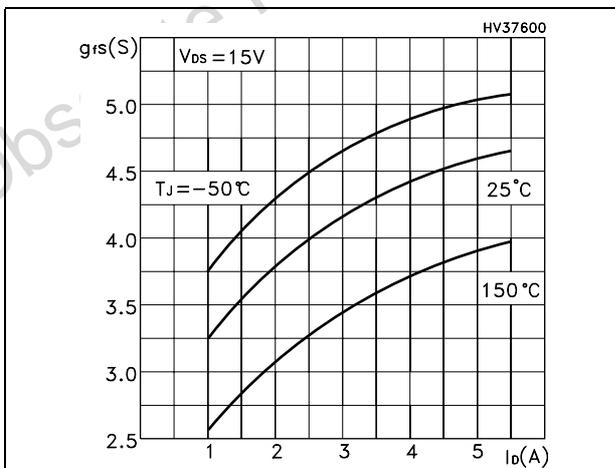


Figure 7. Static drain-source on resistance

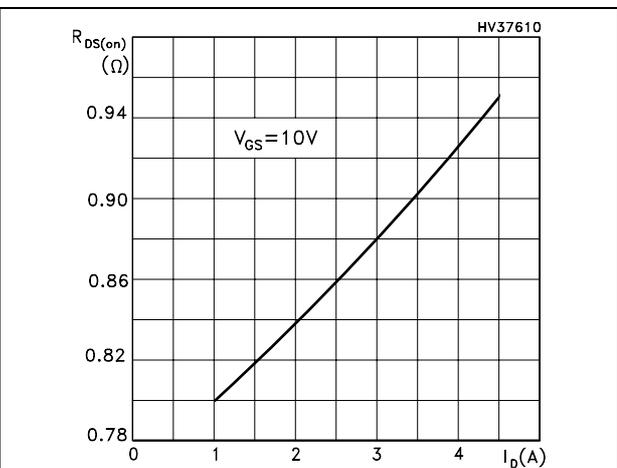


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

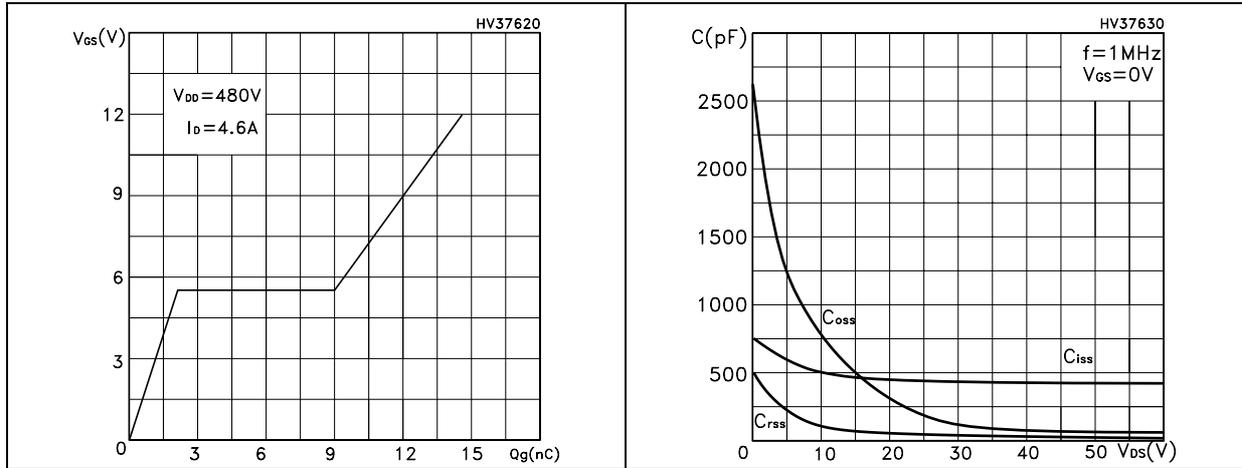


Figure 10. Normalized gate threshold voltage vs temperature

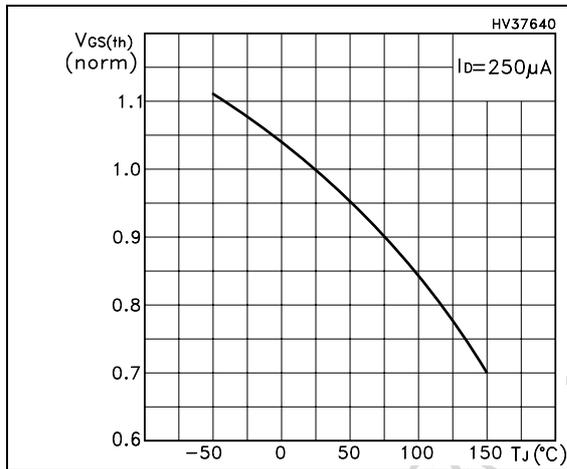


Figure 11. Normalized on resistance vs temperature

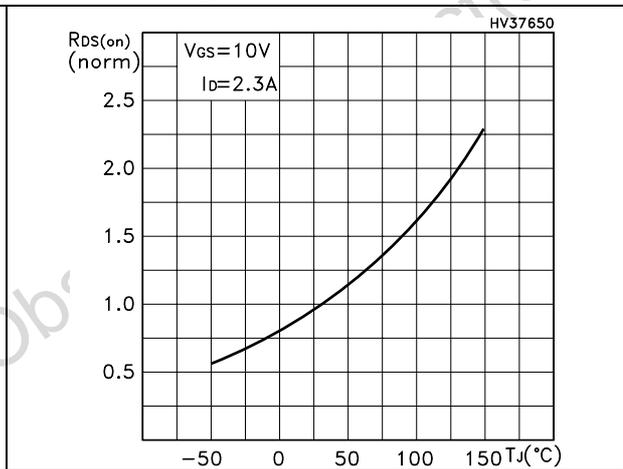


Figure 12. Source-drain diode forward characteristics

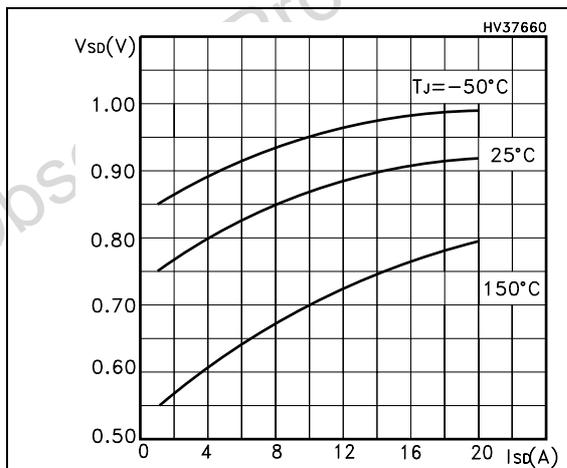
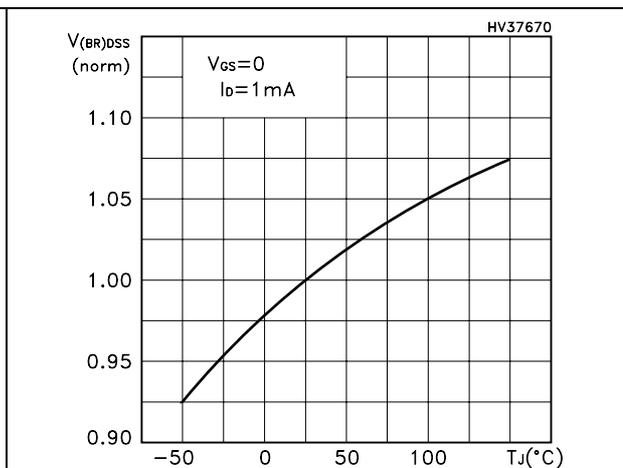


Figure 13. Normalized  $B_{V_{DS}}$  vs temperature



### 3 Test circuit

Figure 14. Switching times test circuit for resistive load

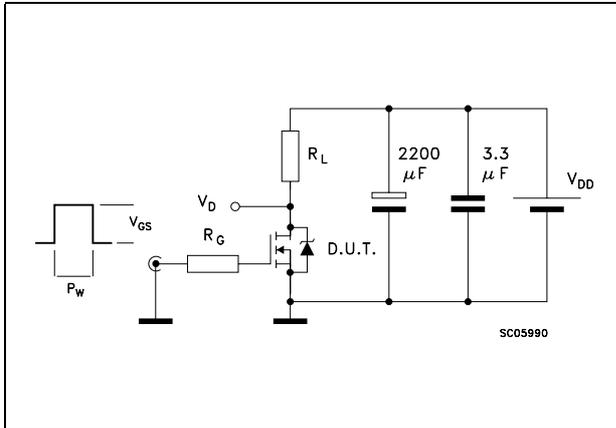


Figure 15. Gate charge test circuit

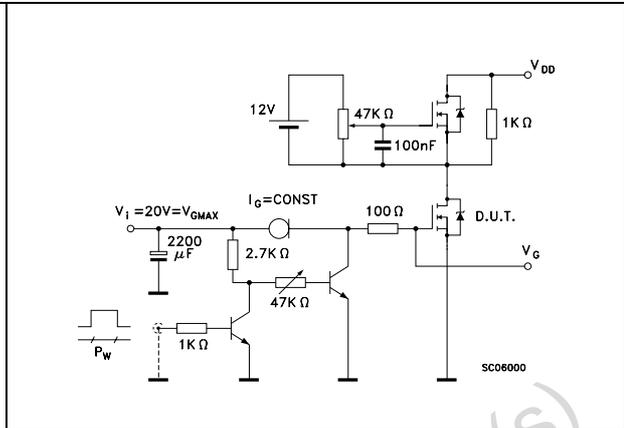


Figure 16. Test circuit for inductive load switching and diode recovery times

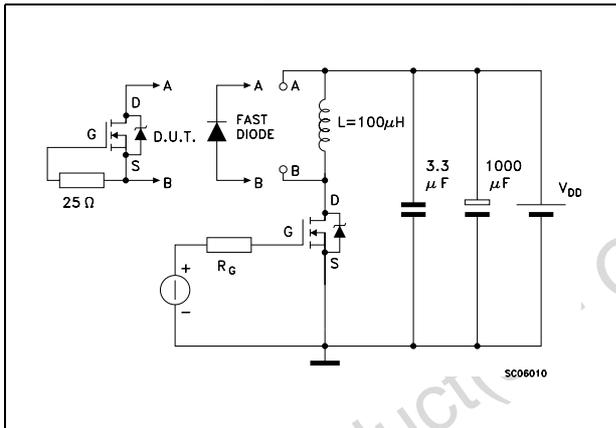


Figure 17. Unclamped inductive load test circuit

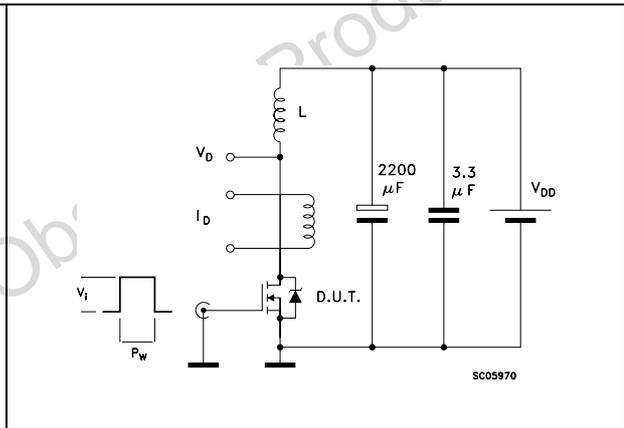


Figure 18. Unclamped inductive waveform

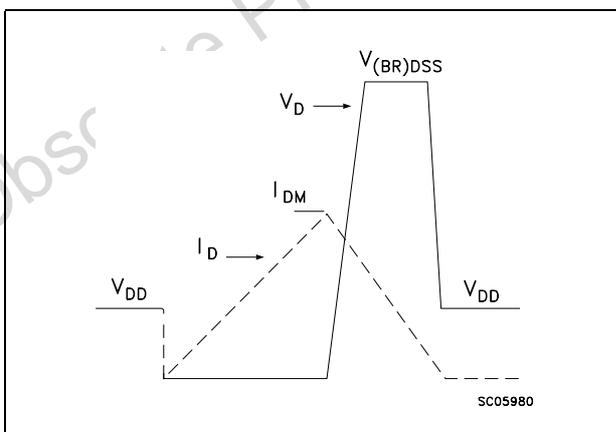
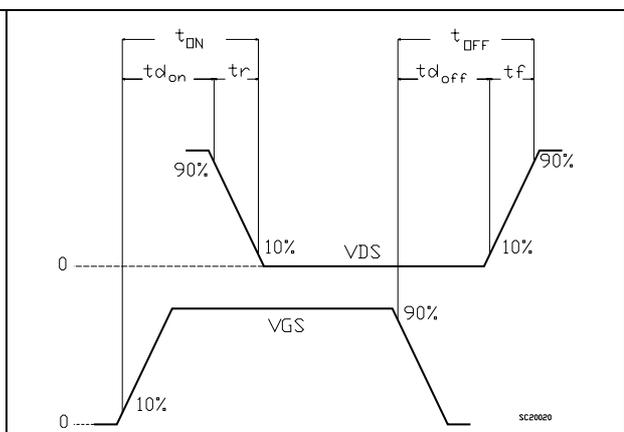


Figure 19. Switching time waveform



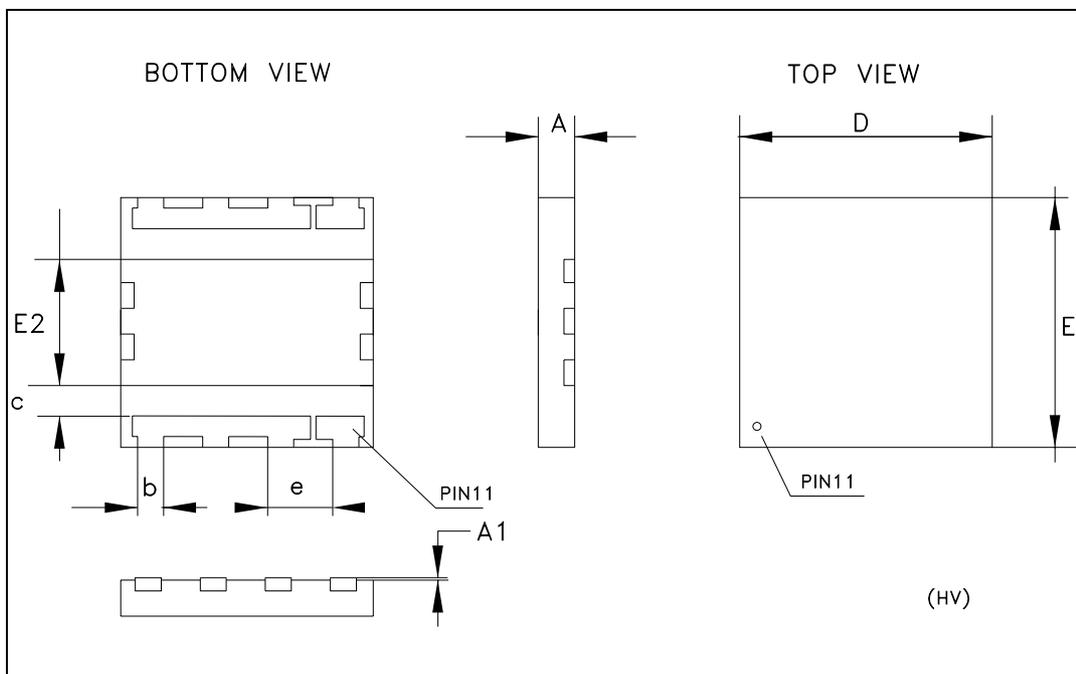
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

Obsolete Product(s) - Obsolete Product(s)

**PowerFLAT™(5x5) MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.80	0.90	1.00	0.031	0.035	0.039
A1		0.02	0.05		0.0007	0.002
A3		0.24			0.009	
b	0.43	0.51	0.58	0.016	0.020	0.022
c	0.64	0.71	0.79	0.025	0.027	0.031
D		5.00			0.19	
E		5.00			0.19	
E2	2.49	2.57	2.64	0.01	0.10	0.103
e		1.27			0.05	



## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
04-May-2007	1	First release
23-May-2007	2	Update test conditions on <a href="#">Table 7</a>
27-Nov-2007	3	Mechanical data has been updated

Obsolete Product(s) - Obsolete Product(s)

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